

SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company



N-Channel Silicon MOSFET BFL4026 — General-Purpose Switching Device **Applications**

Features

• ON-resistance $R_{DS}(on)=2.8\Omega$ (typ.)

• Input capacitance Ciss=650pF (typ.)

Specifications

• 10V drive

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		900	V
Gate-to-Source Voltage	VGSS		±30	V
Drain Current (DC)	I _{Dc} *1	Limited only by maximum temperature Tch=150°C	5	А
	I _{Dpack} *2	Tc=25°C (SANYO's ideal heat dissipation condition)*3	3.5	А
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	10	А
Allowable Power Dissipation	PD		2.0	W
		Tc=25°C (SANYO's ideal heat dissipation condition)*3	35	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *4	EAS		132	mJ
Avalanche Current *5	IAV		5	А

Note :*1 Shows chip capability

*2 Package limited

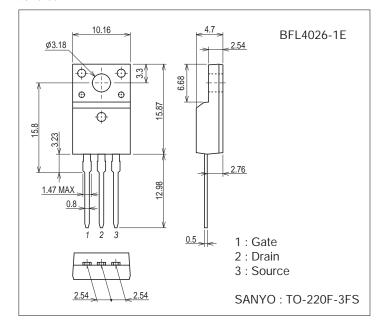
*3 SANYO's condition is radiation from backside.

The method is applying silicone grease to the backside of the device and attaching the device to water-cooled radiator made of aluminium. *4 VDD=50V, L=10mH, IAV=5A (Fig.1)

*5 L≤10mH, single pulse

Package Dimensions

unit : mm (typ) 7528-001



Product & Package Information

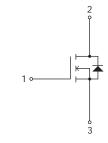
- : TO-220F-3FS Package
- JEITA, JEDEC : SC-67

• Minimum Packing Quantity : 50 pcs./magazine

Marking

Electrical Connection





SANYO Semiconductor Co., Ltd. http://semicon.sanyo.com/en/network

Parameter	Cumpheal			Ratings		
	Symbol	Conditions	min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=10mA, VGS=0V	900			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =720V, V _{GS} =0V			1.0	mA
Gate-to-Source Leakage Current	IGSS	V _{GS} =±30V, V _{DS} =0V			±100	nA
Cutoff Voltage	V _{GS} (off)	V _{DS} =10V, I _D =1mA	2.0		4.0	V
Forward Transfer Admittance	yfs	VDS=20V, ID=2.5A	1.4	2.8		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)	ID=2.5A, VGS=10V		2.8	3.6	Ω
Input Capacitance	Ciss			650		pF
Output Capacitance	Coss	V _{DS} =30V, f=1MHz		100		pF
Reverse Transfer Capacitance	Crss			35		рF
Turn-ON Delay Time	t _d (on)			14		ns
Rise Time	tr			37		ns
Turn-OFF Delay Time	t _d (off)	See Fig.2		117		ns
Fall Time	tf			39		ns
Total Gate Charge	Qg			33		nC
Gate-to-Source Charge	Qgs	V _{DS} =200V, V _{GS} =10V, I _D =5A		5.3		nC
Gate-to-Drain "Miller" Charge	Qgd			16.5		nC
Diode Forward Voltage	V _{SD}	IS=5A, VGS=0V		0.85	1.2	V
Reverse Recovery Time	t _{rr}	See Fig.3		720		ns
Reverse Recovery Charge	Q _{rr}	IS=5A, VGS=0V, di/dt=100A/µs		4700		nC

Fig.1 Avalanche Resistance Test Circuit

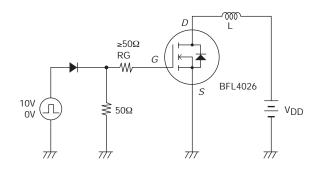
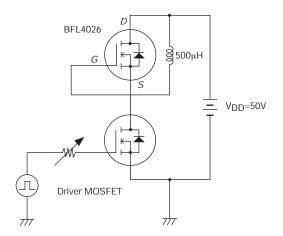


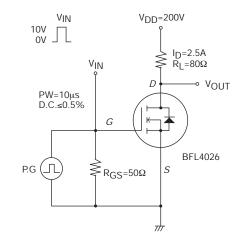
Fig.3 Reverse Recovery Time Test Circuit



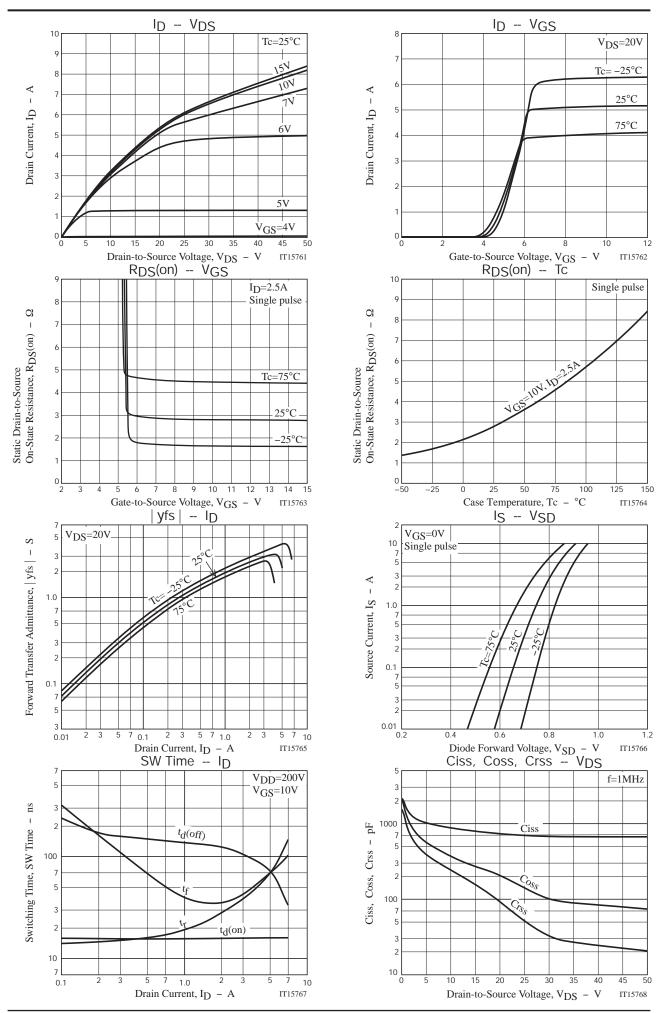
Ordering Information

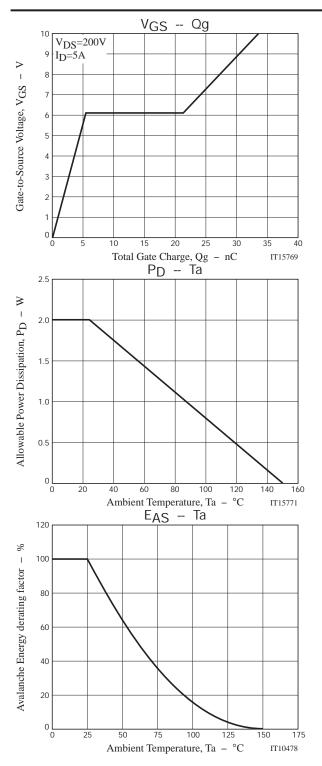
Device	Device Package		memo	
BFL4026-1E	TO-220F-3FS	50pcs./magazine	Pb Free	

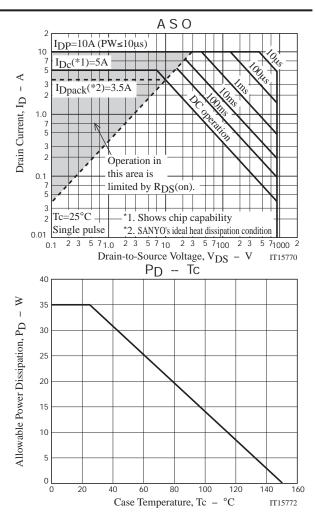
Fig.2 Switching Time Test Circuit



BFL4026







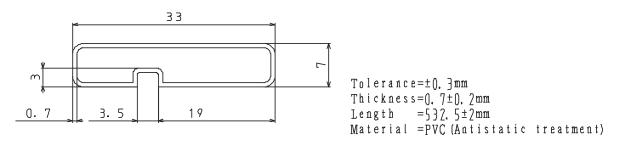
Magazine Specification BFL4026-1E

1. Packing Format

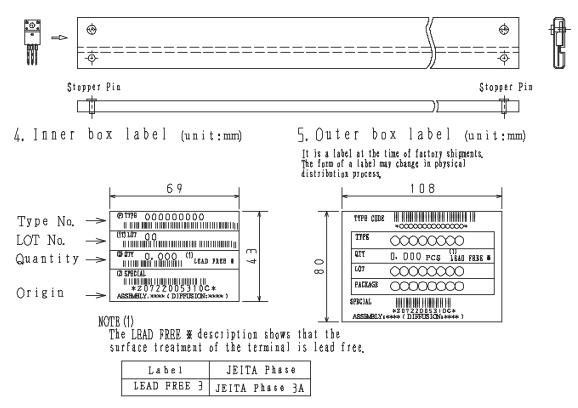
Package Name Magazine Name		Maximum Number of devices contained (pcs)			Packing format		
			Inner box	Quter dax	Inner BOX	Outer BOX	
TO-220F-3F\$	TO-220F	50	1,000	4,000	SPD-0V0001 20 magazines contained Dimensions:mm (external) 568×150×55	SPT-081029 4 inner boxes contained Dimensions:mm {external} 590×225×178	

2. Magazine dimensions

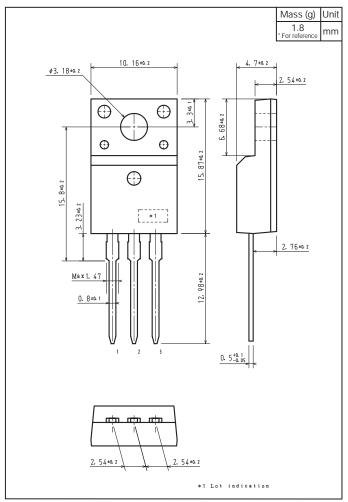
(unit:mm)



3. Storage method to magazine



Outline Drawing BFL4026-1E



Note on usage : Since the BFL4026 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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